

Ultra-Low Voltage Operation Omnipolar Detection

Type Hall Effect Switch IC

General Description

The ET3725A30 is a high sensitivity and high-accuracy Omnipolar Hall effect switch IC that operates at an ultra-low voltage and low current consumption. ET3725A30 has two CMOS output terminal for N and S pole. The output voltage will be pulled low when this IC detects the magnetic flux density is larger than operate point(B_{OPN}/B_{OPS}) and the output voltage will recover to high until the magnetic flux density is smaller than the release point(B_{RPN}/B_{RPS}). Using this IC with a magnet makes it possible to detect the open / close status in various applications.

To achieve a high-density mounting the ET3725A30 uses a super-small DFN4 package.

The ET3725A30 is suitable for battery powered portable devices such as mobile phones and portable PCs etc. due to its low voltage operation and low current consumption, the average current consumption is only typ. 10 μ A with a 1.2V supply.

Features

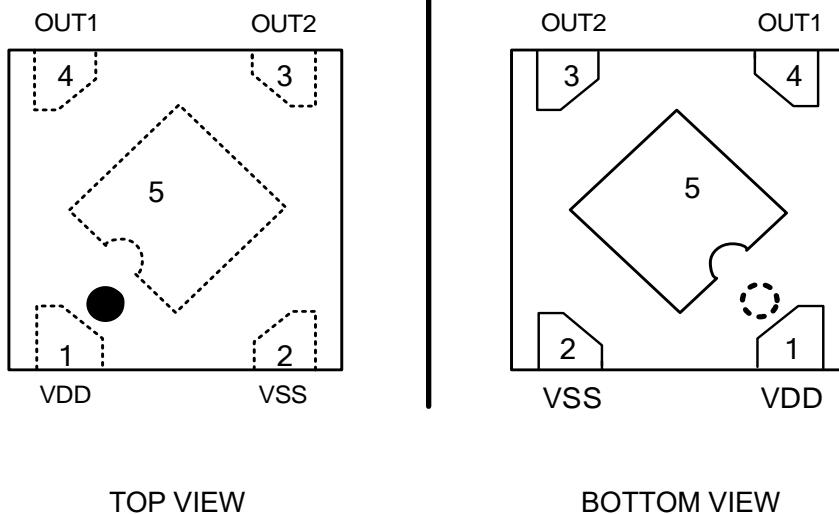
- Pole detection: Omnipolar pole
- Output logic: Dual active low output for N/S-pole
- Output form: CMOS output, no external pull-up resistor required
- Operating Point: $B_{OP} = 3.0$ mT typ.
- Operating cycle: $t_{CYCLE} = 5.70$ ms typ.
- Current consumption: $I_{DD} = \text{typ. } 10.0 \mu\text{A}$ at 1.2 V
- Power supply voltage range: $V_{DD} = 1.0$ V to 3.5 V
- Operation temperature range: $T_A = -40^\circ\text{C}$ to $+85^\circ\text{C}$
- Lead-free (Sn 100%), halogen-free
- Super small DFN4 (1mm x1mm) package

Application

- Open/Close detection for flip mobile phones
- Smart cover for smart phones
- Smart cover for portable PCs, tablet PCs
- Digital video cameras and portable game consoles
- Home appliances

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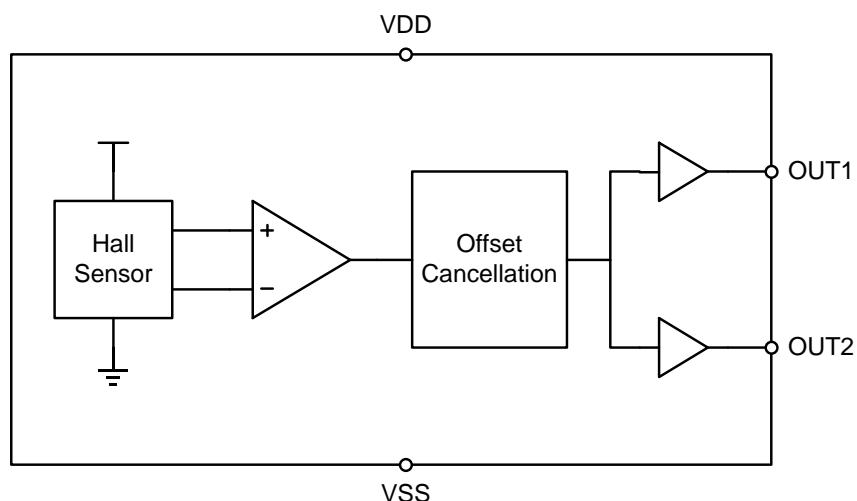
Pin Configuration



Pin Function

Pin No.	Pin Name	Pin Function
1	VDD	Power supply pin
2	VSS	Ground Pin
3	OUT2	S Pole Detection Output pin
4	OUT1	N Pole Detection Output pin
5	Thermal Pad	Leave floating

Block Diagram



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Functional Description

Applied magnetic flux

The magnetic flux applied to ET3725A30 should be in the vertical direction on marking surface. If not, the horizontal component has no effect to detection. ET3725A30 is omnipolar type detector, the corresponding output voltage is inverted when the sufficient S or N type magnetic flux is applied to IC.

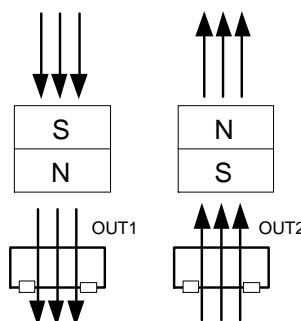


Figure 1. Magnetic Flux Direction

Hall sensor Position

The Hall sensor embedded in ET3725A30 is at the center of IC. As shown below, the position of this Hall sensor is located in the area indicated by a circle, the diameter size of which is about 0.3 mm.

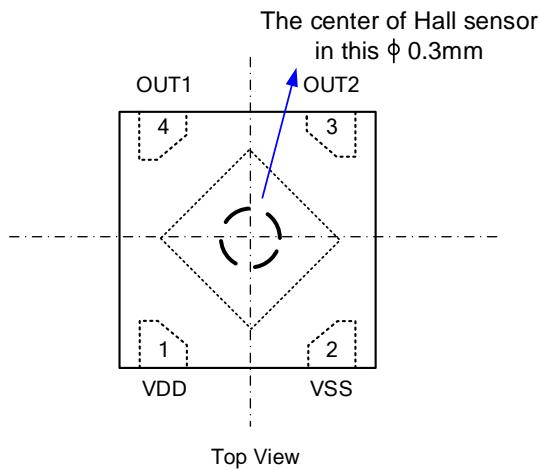


Figure 2. Hall Sensor Position

Detecting Operation

ET3725A30 detects magnetic field periodically. When vertical component of the magnetic flux applied to IC exceeds the operating point (B_{OPN} or B_{OPS}) such as the S or N pole of a magnet is moved closer to IC, V_{OUT} changes from "H" to "L". On the contrary, if magnetic flux is lower than the release point (B_{RPN} or B_{RPS}), V_{OUT} changes from "L" to "H".

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The relationship between the magnetic flux density and V_{OUT} is shown below.

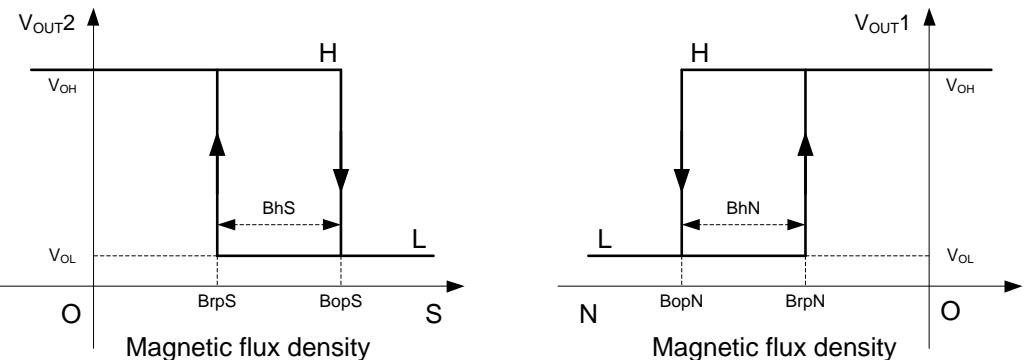


Figure 3. Magnetic Flux Density vs V_{OUT}

Operating Current

ET3725A30 performs the intermittent operation, therefore the average current consumption depends on the current in active mode, the active period (t_{AW}), the current in sleep mode, and sleep period(t_{SL}). The active current is about 640 μ A typically, and 0.72 μ A at sleep mode. Please refer to electrical characteristic table for detail.

The time dependency of the current consumption is shown below.

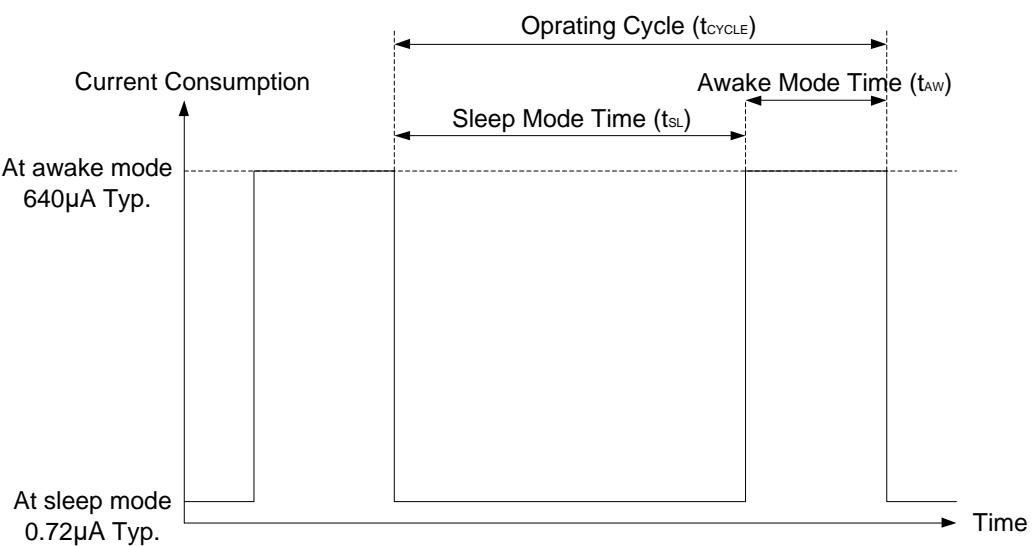


Figure 4. Operating Current

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Timing Diagram

The operation timing of this IC is shown below.

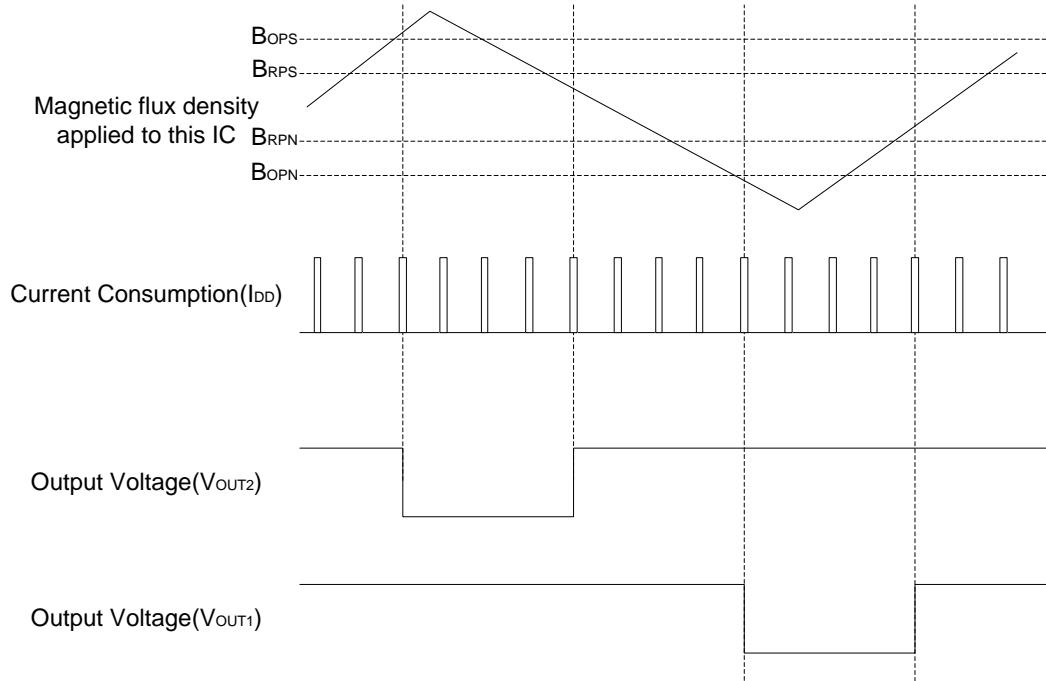


Figure 5. Timing Diagram

Absolute Maximum Ratings

(T_A = +25°C unless otherwise specified)

Symbol	Parameters	Rating	Unit
V _{DD}	Power supply voltage	V _{SS} -0.3 ~ V _{SS} +4.5	V
I _{OUT}	Output current	±1.0	mA
V _{OUT}	Output voltage	V _{SS} - 0.3 ~ V _{DD} + 0.3	V
T _A	Operation ambient temperature	-40 ~ +85	°C
T _{STG}	Storage temperature	-40 ~ +125	°C
θ _{JA}	Junction-to-ambient thermal resistance	250	°C/W

Note: The absolute maximum ratings are rated values exceeding which the product could suffer physical damage. These values must therefore not be exceeded under any conditions.

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Electrical Characteristics

($T_A = +25^\circ\text{C}$, $V_{DD} = 1.2 \text{ V}$, unless otherwise specified)

Symbol	Parameters	Conditions		Min	Typ	Max	Unit
V_{DD}	Power supply voltage	-		1.0	1.2	3.5	V
I_{DD}	Current consumption	Average Supply Current	$V_{DD}=1.2\text{V}$		10.0	16.0	μA
			$V_{DD}=1.8\text{V}$		12.0	18.0	
V_{OL}	Output voltage	CMOS output OUT1,OUT2	$I_{OUT} = 0.5\text{mA}$			0.4	V
			$I_{OUT} = -0.5\text{mA}$	$V_{DD}-0.4$			V
t_{AW}	Awake mode time				0.10		ms
t_{SL}	Sleep mode time				5.60		ms
t_{CYCLE}	Operating cycle	$t_{AW} + t_{SL}$			5.70	12.00	ms

Magnetic Characteristics

($T_A = +25^\circ\text{C}$, $V_{DD} = 1.2 \text{ V}$, unless otherwise specified)

Parameters	Symbol	Conditions	Min	Typ	Max	Unit
Operation point ⁽¹⁾	S pole	B_{OPS}	1.4	3.0	4.0	$\text{mT}^{(4)}$
	N pole	B_{OPN}	-4.0	-3.0	-1.4	mT
Release point ⁽²⁾	S pole	B_{RPS}	1.1	2.2	3.7	mT
	N pole	B_{RPN}	-3.7	-2.2	-1.1	mT
Hysteresis width ⁽³⁾	S pole	B_{HS}	$B_{HS} = B_{OPS} - B_{RPS}$	0.8		mT
	N pole	B_{HN}	$B_{HN} = B_{OPN} - B_{RPN} $	0.8		mT

Notes:

(1) Operating points (B_{OPN} , B_{OPS}): B_{OPN} and B_{OPS} are the values of magnetic flux density triggers the output voltage (V_{OUT}) to low by increasing the N pole or S pole magnetic flux density applied to this IC. Even when the magnetic flux density is larger than B_{OPN} or B_{OPS} , V_{OUT} status is held.

(2) Release points (B_{RPN} , B_{RPS}): B_{RPN} and B_{RPS} are the values of magnetic flux density makes the output voltage (V_{OUT}) recover to high by decreasing the N pole or S pole magnetic flux density applied to this IC. Even when the magnetic flux density is lower than B_{RPN} or B_{RPS} , V_{OUT} status is held.

(3) Hysteresis widths (B_{HN} , B_{HS}): B_{HN} and B_{HS} are the difference between B_{OPN} and B_{RPN} , and B_{OPS} and B_{RPS} , respectively.

(4) The unit of magnetic density mT can be converted by using the formula $1 \text{ mT} = 10 \text{ Gauss}$.

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Application Circuit

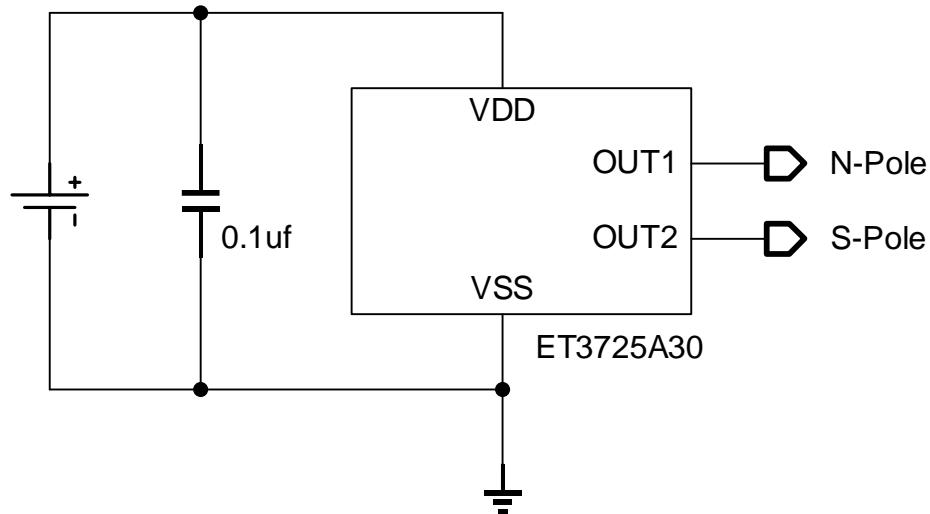


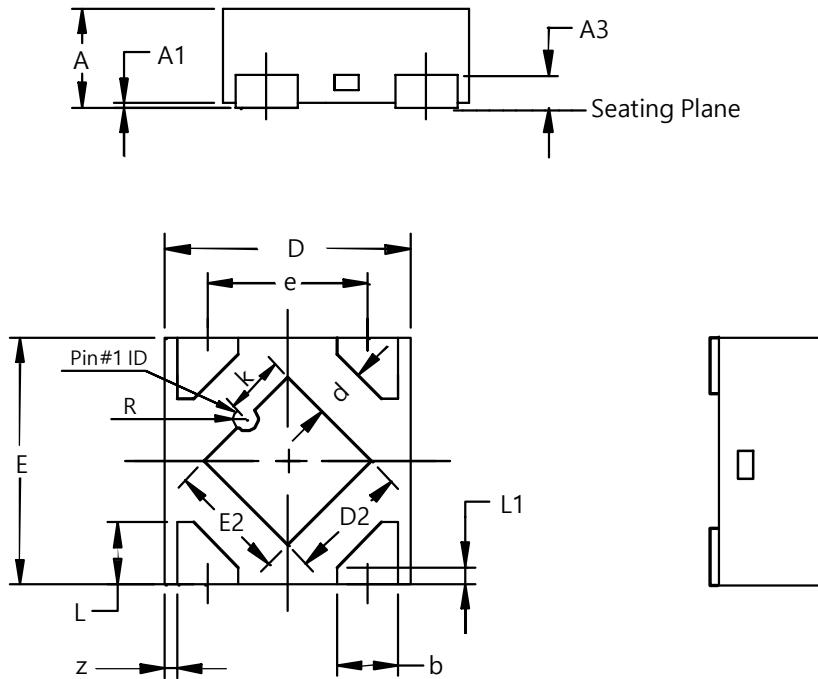
Figure 6. Application Circuit

Precautions

- The power supply for this IC should have low impedance, the IC may malfunction due to a supply voltage drop caused by feed through current.
- Power supply voltage rapidly changing may cause IC malfunction.
- Large stress on this IC may affect the magnetic characteristics. Avoid large stress applied to the IC on a board.
- Thermal pad need floating .

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Package Dimension

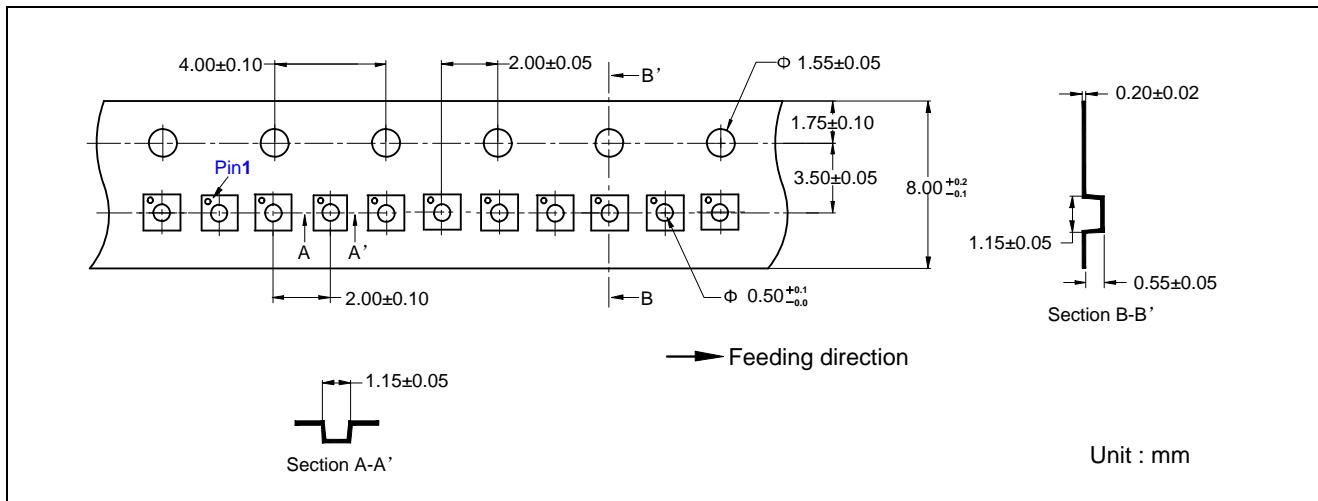


COMMON DIMENSIONS
(UNITS OF MEASURE=MILLIMETER)

SYMBOL	MIN	NOM	MAX
A	>0.3	0.38	0.40
A1	0.00	0.03	0.05
A3	0.127REF		
b	0.20	0.25	0.30
D	0.95	1.00	1.05
D2	0.43	0.48	0.53
E	0.95	1.00	1.05
E2	0.43	0.48	0.53
d	-	0.205	-
e	0.65BSC		
k	0.19	0.24	0.29
L	0.15	0.25	0.35
L1	0.02	0.07	0.12
R	0.02	0.05	0.08
z	-	0.050	-

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Reel



Pocket

Package	Qty	Carrier
DFN4(1x1)	10000	7" Tape and Reel

Revision History and Checking Table

Version	Date	Revision Item	Modifier	Function & Spec Checking	Package & Tape Checking
0.0	2024.5.30	Preliminary Version	Zhangy	Wanggp	Liujy
1.0	2024.12.27	Released Version	Zhangy	Wanggp	Liujy